



Phonons in Ge/Si quantum dot structures: influence of growth temperature

A. G. Milekhin  ^a, A. I. Nikiforov^a, M. Yu. Ladanov^a, O. P. Pchelyakov^a, D. N. Lobanov^b, A. V. Novikov^b, Z. F. Krasil'nik^b, S. Schulze^c and D. R. T. Zahn^c

^a Institute of Semiconductor Physics, Lavrentjev av.13, Novosibirsk 630090, Russia

^b Institute for Physics of Microstructures, Russian Academy of Sciences, Nizhny Novgorod 603950, Russia

^c Institut für Physik, Technische Universität Chemnitz, D-09107, Chemnitz, Germany


Available online 3 February 2004.

Abstract

In this paper we present the results of a Raman study of Ge/Si quantum dot (QD) superlattices grown with different thicknesses of a Si interlayer and at different substrate temperatures. The built-in strain and atomic intermixing in the QDs are deduced from an analysis of optical phonon frequencies of the QDs obtained from Raman spectra of the structures.

Author Keywords: Author Keywords: Raman spectroscopy; Phonons; Quantum dots; Confinement

78.30.Am; 78.67.Hc

 Corresponding author. Tel.: +007-3832-34-35-91; fax: +007-3832-33-27-71